

ABSTRACT OF THE DISCLOSURE

The invention aims to provide a semiconductor device and a method for manufacturing the same that are capable of improving the product performance and operational efficiency of a cross-point FeRAM as well as increasing the area of capacitors included in the cross-point FeRAM. An upper electrode supporting layer forming mask M1 for forming an upper electrode supporting layer 2C is made of a hard mask material. By making use of the upper electrode supporting layer forming mask M1 remaining unremoved in forming and processing a lower electrode layer 2A, prior to forming an upper electrode layer 2D, a region where a ferroelectric capacitor C is formed is made larger than an area occupied by an intersection of the upper electrode layer 2D and the lower electrode layer 2A.